

CD4073B, CD4081B, CD4082B Types

CMOS AND Gates

High-Voltage Types (20-Volt Rating)

CD4073B Triple 3-Input AND Gate

CD4081B Quad 2-Input AND Gate

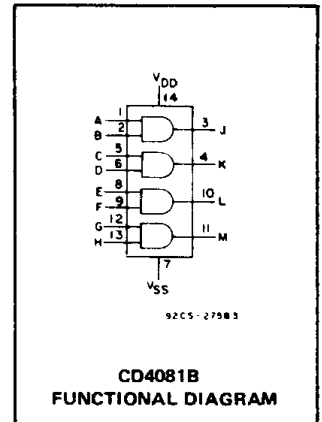
CD4082B Dual 4-Input AND Gate

The RCA-CD4073B, CD4081B and CD-4082B AND gates provide the system designer with direct implementation of the AND function and supplement the existing family of CMOS gates.

The CD4073B, CD4081B and CD4082B types are supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

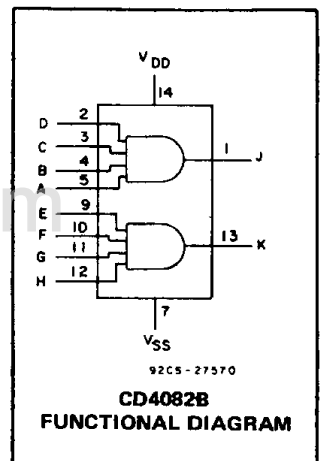
Features:

- Medium-Speed Operation — t_{PLH} , $t_{PHL} = 60$ ns (typ.) at $V_{DD} = 10$ V
- 100% tested for quiescent current at 20 V
- Maximum input current of $1 \mu A$ at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) =
 - 1 V at $V_{DD} = 5$ V
 - 2 V at $V_{DD} = 10$ V
 - 2.5 V at $V_{DD} = 15$ V
- Standardized, symmetrical output characteristics
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) (Voltages referenced to V_{SS} Terminal)	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT	± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -40$ to $+60^\circ C$ (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85^\circ C$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ C$ to 200 mW
For $T_A = -55$ to $+100^\circ C$ (PACKAGE TYPES D, F, K)	500 mW
For $T_A = +100$ to $+125^\circ C$ (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/ $^\circ C$ to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES D, F, K, H	-55 to $+125^\circ C$
PACKAGE TYPE E	-40 to $+85^\circ C$
STORAGE TEMPERATURE RANGE (T_{stg})	-65 to $+150^\circ C$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10 s max.	$+265^\circ C$



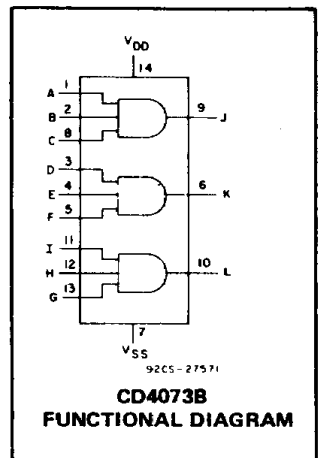
RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A =$ Full Package Temperature Range)	3	18	V

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ C$, Input $t_r, t_f = 20$ ns, and $C_L = 50$ pF, $R_L = 200$ k Ω

CHARACTERISTIC	TEST CONDITIONS	ALL TYPES LIMITS			UNITS
		V_{DD} Volts	TYP.	MAX.	
Propagation Delay Time, t_{PHL}, t_{PLH}		5	125	250	ns
		10	60	120	
		15	45	90	
Transition Time, t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{IN}	Any Input	-	5	7.5	pF



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STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	Values at -55, +25, +125 Apply to D, F, K, H Packages				Values at -40, +25, +85 Apply to E Package			
				-55	-40	+85	+125	+25			
				Min.	Typ.	Max.					
Quiescent Device Current, I _{DD} Max.	-	0,5	5	0,25	0,25	7,5	7,5	-	0,01	0,25	μA
	-	0,10	10	0,5	0,5	15	15	-	0,01	0,5	
	-	0,15	15	1	1	30	30	-	0,01	1	
	-	0,20	20	5	5	150	150	-	0,02	5	
Output Low (Sink) Current I _{OL} Min.	0,4	0,5	5	0,64	0,61	0,42	0,36	0,51	1	-	mA
	0,5	0,10	10	1,6	1,5	1,1	0,9	1,3	2,6	-	
	1,5	0,15	15	4,2	4	2,8	2,4	3,4	6,8	-	
Output High (Source) Current, I _{OH} Min.	4,6	0,5	5	-0,64	-0,61	-0,42	-0,36	-0,51	-1	-	mA
	2,5	0,5	5	-2	-1,8	-1,3	-1,15	-1,6	-3,2	-	
	9,5	0,10	10	-1,6	-1,5	-1,1	-0,9	-1,3	-2,6	-	
	13,5	0,15	15	-4,2	-4	-2,8	-2,4	-3,4	-6,8	-	
Output Voltage: Low-Level, V _{OL} Max.	-	0,5	5	0,05				-	0	0,05	V
	-	0,10	10	0,05				-	0	0,05	
	-	0,15	15	0,05				-	0	0,05	
Output Voltage: High-Level, V _{OH} Min.	-	0,5	5	4,95				4,95	5	-	V
	-	0,10	10	9,95				9,95	10	-	
	-	0,15	15	14,95				14,95	15	-	
Input Low Voltage, V _{IL} Max.	0,5	-	5	1,5				-	-	1,5	V
	1	-	10	3				-	-	3	
	1,5	-	15	4				-	-	4	
Input High Voltage, V _{IH} Min.	0,5, 4,5	-	5	3,5				3,5	-	-	V
	1,9	-	10	7				7	-	-	
	1,5, 13,5	-	15	11				11	-	-	
Input Current I _{IN} Max.		0,18	18	±0,1	±0,1	±1	±1	-	±10 ⁻⁵	±0,1	μA

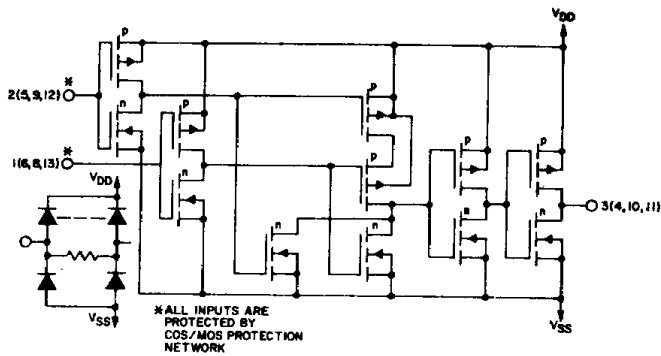


Fig. 1 - Schematic diagram for CD4081B (1 of 4 identical gates).

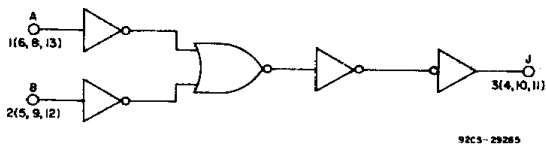


Fig. 2 - Logic diagram for CD4081B (1 of 4 identical gates).

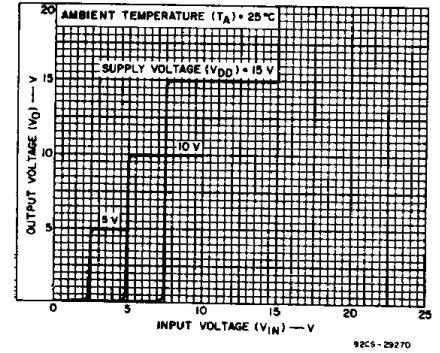


Fig. 3 - Typical voltage transfer characteristics.

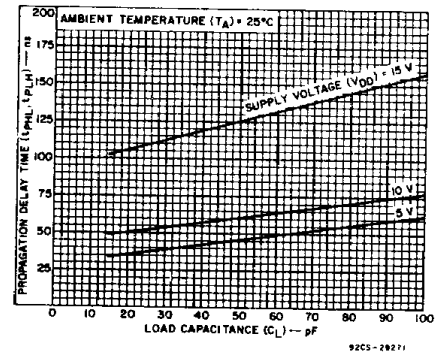


Fig. 4 - Typical propagation delay time as a function of load capacitance.

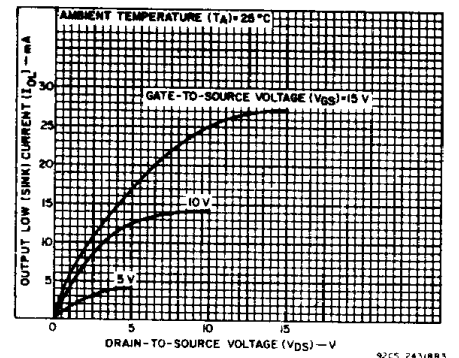


Fig. 5 - Typical output low (sink) current characteristics.

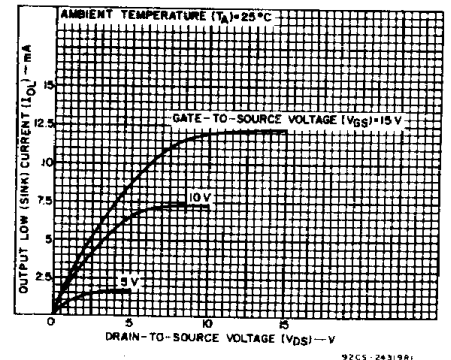


Fig. 6 - Minimum output low (sink) current characteristics.

CD4073B, CD4081B, CD4082B Types

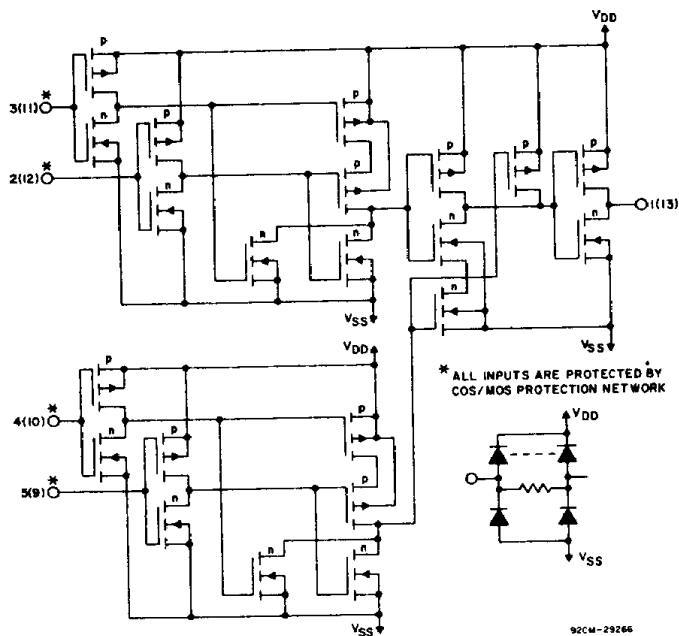


Fig. 7 - Schematic diagram for CD4082B (1 of 2 identical gates).

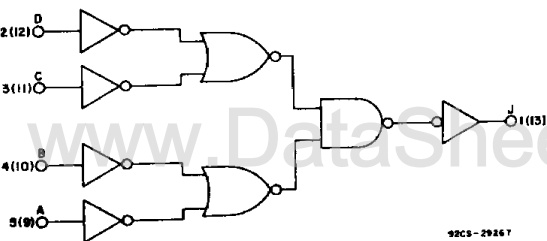


Fig. 9 - Logic diagram for CD4082B (1 of 2 identical gates).

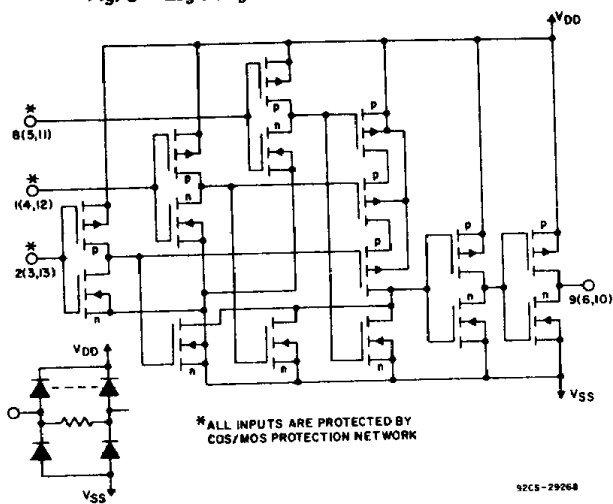


Fig. 11 - Schematic diagram for CD4073B (1 of 3 identical gates).

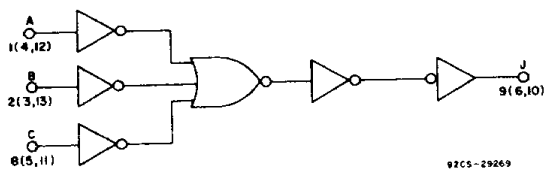


Fig. 13 - Logic diagram for CD4073B (1 of 3 identical gates).

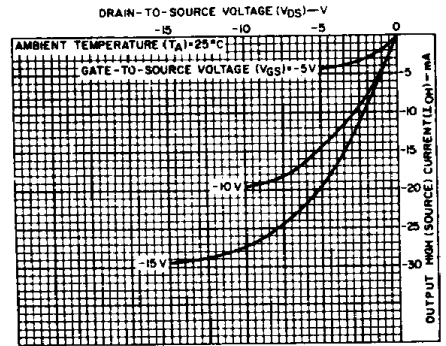


Fig. 8 - Typical output high (source) current characteristics.

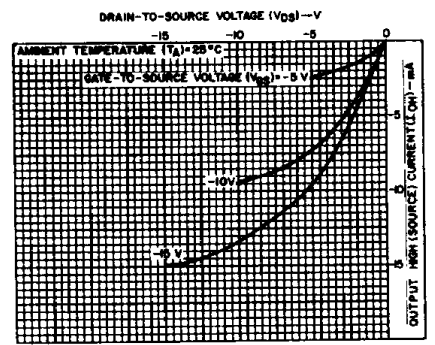


Fig. 10 - Minimum output high (source) current characteristics.

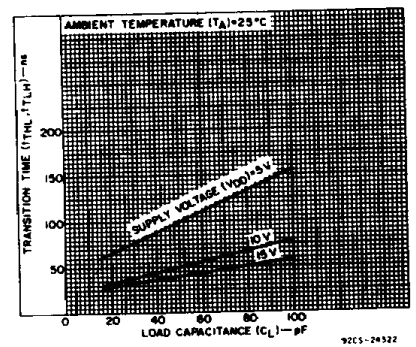


Fig. 12 - Typical transition time as a function of load capacitance.

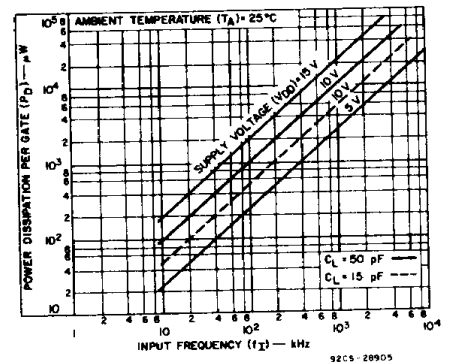


Fig. 14 - Typical dynamic power dissipation per gate as a function of frequency.

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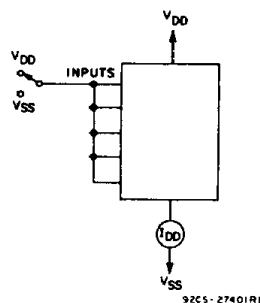


Fig. 15 - Quiescent device current test circuit.

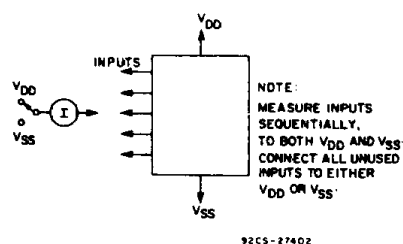


Fig. 16 - Input current test circuit.

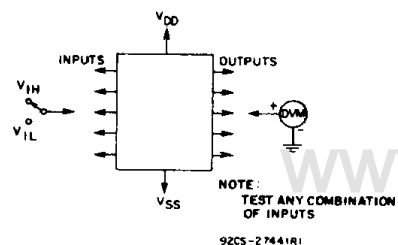
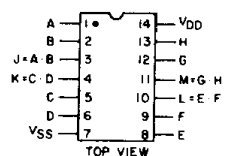


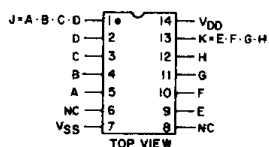
Fig. 17 - Input-voltage test circuit.

TERMINAL ASSIGNMENTS



92CS-24536

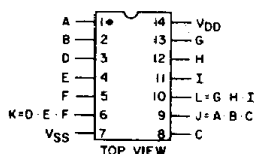
CD4081B



NC=NO CONNECTION

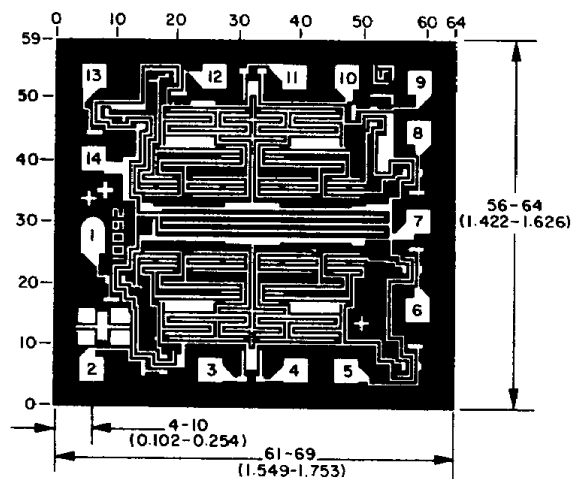
92CS-24537R2

CD4082B

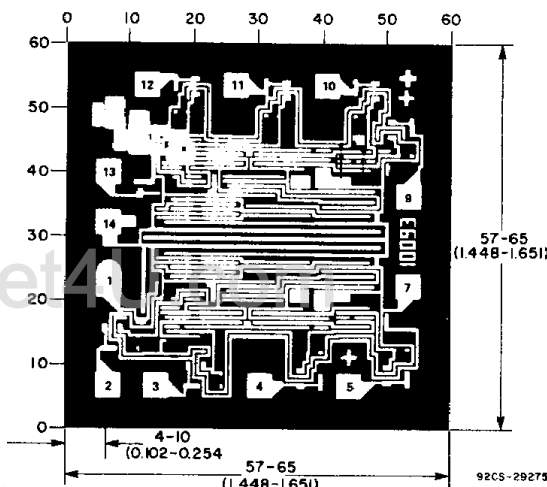


92CS-24538

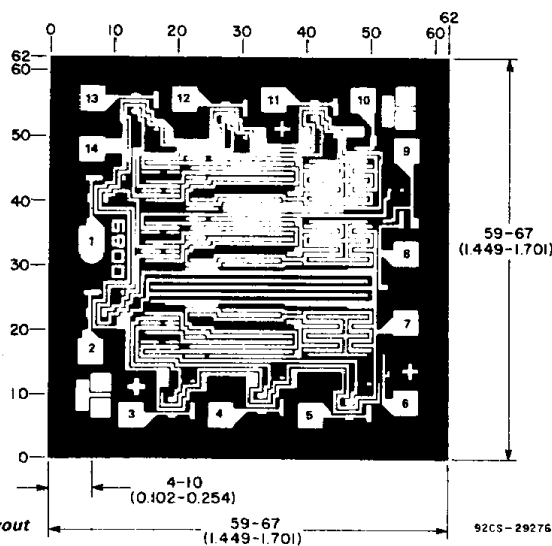
CD4073B



Dimensions and pad layout for CD4081B.



Dimensions and pad layout for CD4082B.



Dimensions and pad layout for CD4073B.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated

chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of -3 mils to $+16$ mils applicable to the nominal dimensions shown.